

Vishay Semiconductors

Schottky Diodes

Features

- For general purpose applications
- These diodes feature very low turn-on voltage and fast guard ring against excessive voltage, such as electrostatic discharges
- These diodes are also available in the SOD-123 case with the type designations BAT42W to BAT43W and in designations LL42 to LL43.



Mechanical Data

Case: DO-35 Glass Case

Weight: 130 mg Packaging Codes/Options:

TR / 10 k per 13 " reel (52 mm tape), 50 k/box

TAP / 10 k per Ammo tape (52 mm tape), 50 k/box

Parts Table

Part	Ordering code	Marking	Remarks
BAT42	BAT42-GS18 or BAT42-GS08	-	Tape and Reel
BAT43	BAT43-GS18 or BAT43-GS08	-	Tape and Reel

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit	
Repetitive peak reverse voltage		V _{RRM}	30	V	
Forward continuous current	T _{amb} = 25 °C	١ _F	200 ¹⁾	mA	
Repetitive peak forward current	$t_p < 1 \text{ s}, \theta < 0.5, T_{amb} = 25 \text{ °C}$	I _{FRM}	500 ¹⁾	mA	
Surge forward current	t_p < 10 ms, T_{amb} = 25 °C	I _{FSM}	4 ¹⁾	A	
Power dissipation ¹⁾	T _{amb} = 65 °C	P _{tot}	200 ¹⁾	mW	

¹⁾ Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature

Thermal Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R _{θJA}	300 ¹⁾	°C/W
Junction temperature		Тj	125	°C
Ambient operating temperature range		T _{amb}	- 65 to + 125	°C
Storage temperature range		Τ _S	- 65 to +150	°C

¹⁾ Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature

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Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Тур.	Max	Unit
Reverse breakdown voltage	$I_R = 100 \ \mu A \ (pulsed)$		V _{(BR)R}	30			V
Leakage current	V _R = 25 V		I _R			0.5	nA
	V _R = 25 V, T _j = 100 °C		۱ _R			100	μΑ
Forward voltage	I _F = 200 mA	BAT42	V _F			1	V
		BAT43	V _F			1	V
	I _F = 10 mA	BAT42	V _F			0.4	V
	I _F = 50 mA	BAT43	V _F			0.65	V
	$I_F = 2 \text{ mA}$	BAT43	V _F	0.26		0.33	V
	I _F = 15 mA	BAT43	V _F			0.45	V
Capacitance	V _R = 1 V, f = 1 MHz		C _{tot}		7		pF
Reverse recovery time	$I_F = 10 \text{ mA}, I_R = 10 \text{ mA},$ $I_{rr} = 1 \text{ mA}, R_L = 100 \Omega$		t _{rr}			5	ns
Detection efficiency	$R_L = 15 k\Omega$, $C_L = 300 pF$, f = 45 MHz, V _{RF} = 2 V		η_v	80			%

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)

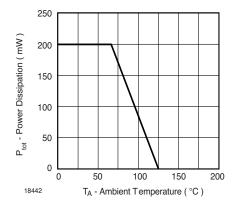


Figure 1. Admissible Power Dissipation vs. Ambient Temperature

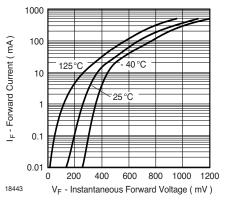


Figure 2. Typical Reverse Characteristics



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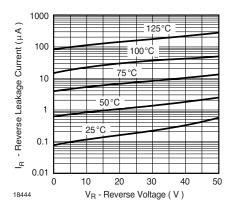


Figure 3. Typical Reverse Characteristics

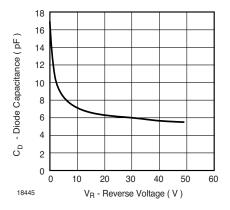
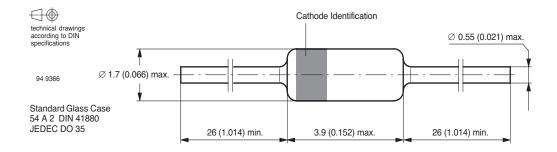


Figure 4. Typical Capacitance vs. Reverse Applied Voltage

Package Dimensions in mm (Inches)



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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